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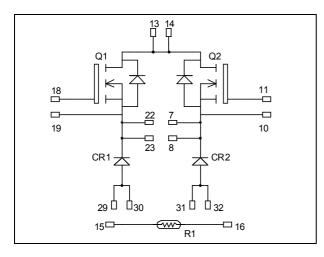
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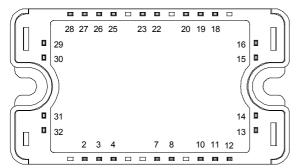
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Dual Buck chopper MOSFET Power Module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

Absolute maximum ratings

Symbol Parameter Max ratings Unit Drain - Source Breakdown Voltage 500 V V_{DSS} $T_c = 25^{\circ}C$ 37 Continuous Drain Current I_D $T_c = 80^{\circ}C$ 28 Α Pulsed Drain current 140 I_{DM} Gate - Source Voltage ± 30 V V_{GS} Drain - Source ON Resistance R_{DSon} 120 mΩ $T_c = 25^{\circ}C$ P_{D} Maximum Power Dissipation 312 W $I_{AR} \\$ Avalanche current (repetitive and non repetitive) 37 А Repetitive Avalanche Energy 50 EAR mJ EAS Single Pulse Avalanche Energy 1600

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

$V_{DSS} = 500V$ $R_{DSon} = 100m\Omega \text{ typ } @ \text{ Tj} = 25^{\circ}C$ $I_{D} = 37A @ \text{ Tc} = 25^{\circ}C$

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single buck of twice the current capability
- RoHS Compliant

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$	$Tj = 25^{\circ}C$			100	μA
		$V_{GS} = 0V, V_{DS} = 400V$	Tj = 125°C			500	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 18.5A$			100	120	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1 \text{ mA}$		3		5	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$				±100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		4367		
C _{oss}	Output Capacitance	$V_{\rm DS} = 25 V$		894		pF
C _{rss}	Reverse Transfer Capacitance	f = 1 MHz		61		
Qg	Total gate Charge	$V_{GS} = 10V$		96		
Q _{gs}	Gate – Source Charge	$V_{Bus} = 250V$		24		nC
Q_{gd}	Gate – Drain Charge	$I_D = 37A$		49		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C		15		
T _r	Rise Time	$V_{GS} = 15V$ $V_{Bus} = 333V$ $I_D = 37A$ $R_G = 5\Omega$		21		
T _{d(off)}	Turn-off Delay Time			73		ns
T_{f}	Fall Time			52		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		566		I
E_{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 37A, R_G = 5\Omega$		545		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		931		
E _{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 37A, R_G = 5\Omega$		635		μJ

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$			250 500	μΑ
I _F	DC Forward Current		$T_c = 80^{\circ}C$		40		А
V _F	Diode Forward Voltage	$I_F = 40A$	$T_i = 25^{\circ}C$		1.45		V
ν _F			$T_{j} = 125^{\circ}C$		1.35		v
t _{rr}	Reverse Recovery Time	$I_{\rm F} = 40 \text{A}$ $V_{\rm R} = 300 \text{V}$	$T_j = 25^{\circ}C$		95		ns
۰rr			$T_{j} = 125^{\circ}C$		115		115
Q _{rr}	Reverse Recovery Charge	di/dt=2600A/µs	$T_j = 25^{\circ}C$		2.6		μC
Zu			$T_{j} = 125^{\circ}C$		4		μΟ

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Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance		Transistor			0.4	°C/W
			Diode			1.5	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		4000			V	
T _J	Operating junction temperature range		-40		150		
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

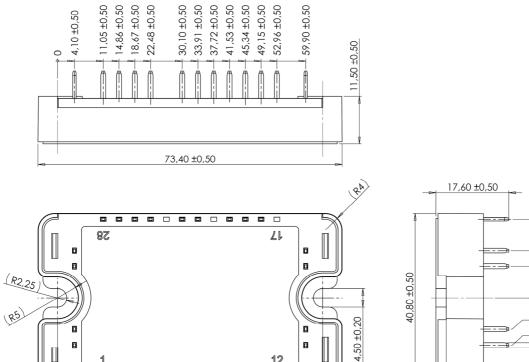
Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

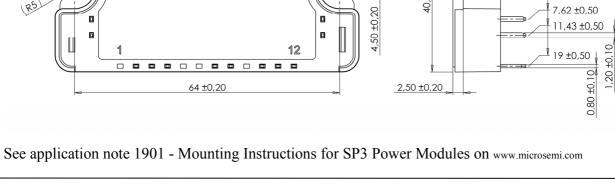
$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP3 Package outline (dimensions in mm)

1

64 ±0,20





19 ±0,50

11,43 ±0,50

7,62 ±0,50

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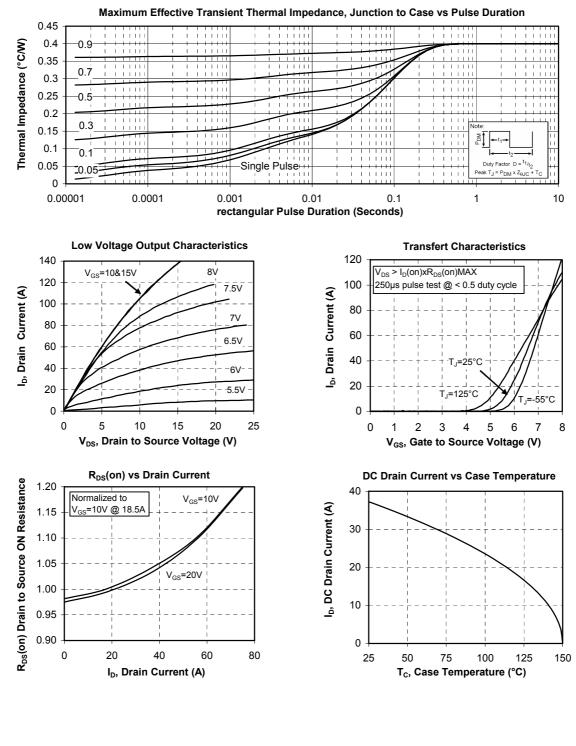
2,50 ±0,20

12

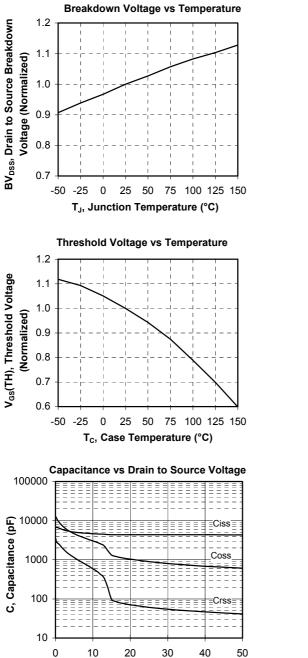
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Typical Performance Curve

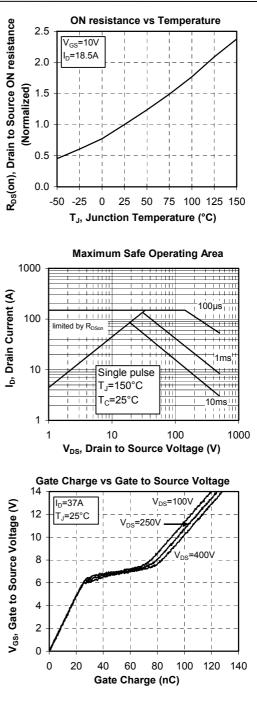






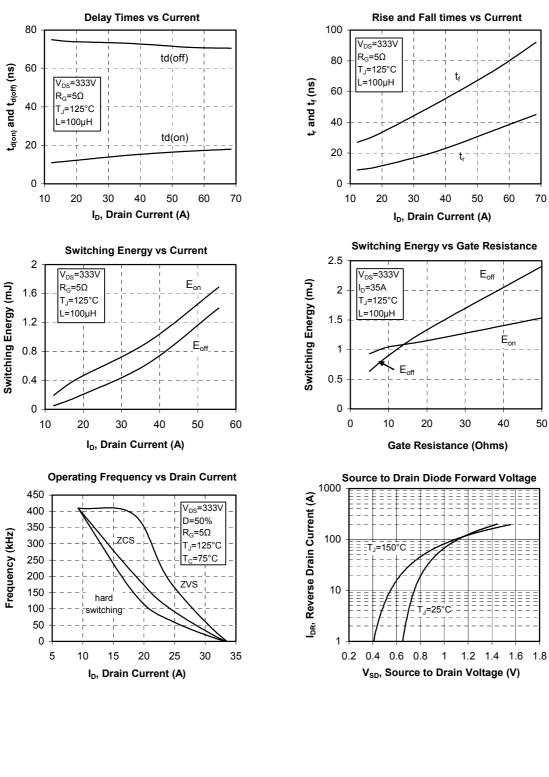
V_{DS}, Drain to Source Voltage (V)

APTM50DSK10T3G



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